



**ALPHA & OMEGA**  
SEMICONDUCTOR



**AO4459**

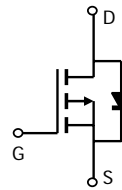
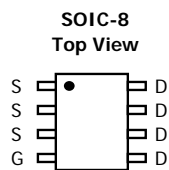
**P-Channel Enhancement Mode Field Effect Transistor**

**General Description**

The AO4459 uses advanced trench technology to provide excellent  $R_{DS(ON)}$  with low gate charge. This device is suitable for use as a load switch or in PWM applications. *Standard product AO4459 is Pb-free (meets ROHS & Sony 259 specifications). AO4459L is a Green Product ordering option. AO4459 and AO4459L are electrically identical.*

**Features**

$V_{DS}$  (V) = -30V  
 $I_D$  = -6.5A ( $V_{GS}$  = -10V)  
 $R_{DS(ON)} < 46m\Omega$  ( $V_{GS}$  = -10V)  
 $R_{DS(ON)} < 72m\Omega$  ( $V_{GS}$  = -4.5V)



**Absolute Maximum Ratings**  $T_A=25^\circ\text{C}$  unless otherwise noted

Parameter	Symbol	Maximum	Units
Drain-Source Voltage	$V_{DS}$	-30	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Continuous Drain Current <sup>A</sup>	$I_D$	-6.5	A
$T_A=25^\circ\text{C}$			
$T_A=70^\circ\text{C}$		-5.3	
Pulsed Drain Current <sup>B</sup>	$I_{DM}$	-30	
Power Dissipation <sup>A</sup>	$P_D$	3.1	W
$T_A=25^\circ\text{C}$			
$T_A=70^\circ\text{C}$		2	
Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 to 150	$^\circ\text{C}$

**Thermal Characteristics**

Parameter		Symbol	Typ	Max	Units
Maximum Junction-to-Ambient <sup>A</sup>	$t \leq 10\text{s}$	$R_{\theta JA}$	33	40	$^\circ\text{C/W}$
Maximum Junction-to-Ambient <sup>A</sup>	Steady-State		62	75	$^\circ\text{C/W}$
Maximum Junction-to-Lead <sup>C</sup>	Steady-State	$R_{\theta JL}$	18	24	$^\circ\text{C/W}$

Electrical Characteristics ( $T_J=25^{\circ}\text{C}$  unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
<b>STATIC PARAMETERS</b>						
$BV_{DSS}$	Drain-Source Breakdown Voltage	$I_D=-250\mu\text{A}$ , $V_{GS}=0\text{V}$	-30			V
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS}=-24\text{V}$ , $V_{GS}=0\text{V}$ $T_J=55^{\circ}\text{C}$			-1 -5	$\mu\text{A}$
$I_{GSS}$	Gate-Body leakage current	$V_{DS}=0\text{V}$ , $V_{GS}=\pm 20\text{V}$			$\pm 100$	nA
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}$ , $I_D=-250\mu\text{A}$	-1.5	-1.85	-2.5	V
$I_{D(ON)}$	On state drain current	$V_{GS}=-10\text{V}$ , $V_{DS}=-5\text{V}$	-30			A
$R_{DS(ON)}$	Static Drain-Source On-Resistance	$V_{GS}=-10\text{V}$ , $I_D=-6.5\text{A}$ $T_J=125^{\circ}\text{C}$		38 53	46 68	$\text{m}\Omega$
		$V_{GS}=-4.5\text{V}$ , $I_D=-5\text{A}$		58	72	$\text{m}\Omega$
		$V_{DS}=-5\text{V}$ , $I_D=-6.5\text{A}$		11		S
$g_{FS}$	Forward Transconductance	$V_{DS}=-5\text{V}$ , $I_D=-6.5\text{A}$		11		S
$V_{SD}$	Diode Forward Voltage	$I_S=-1\text{A}$ , $V_{GS}=0\text{V}$		-0.78	-1	V
$I_S$	Maximum Body-Diode Continuous Current				-3.5	A
<b>DYNAMIC PARAMETERS</b>						
$C_{iss}$	Input Capacitance	$V_{GS}=0\text{V}$ , $V_{DS}=-15\text{V}$ , $f=1\text{MHz}$		668	830	pF
$C_{oss}$	Output Capacitance			126		pF
$C_{rss}$	Reverse Transfer Capacitance			92		pF
$R_g$	Gate resistance	$V_{GS}=0\text{V}$ , $V_{DS}=0\text{V}$ , $f=1\text{MHz}$		6	9	$\Omega$
<b>SWITCHING PARAMETERS</b>						
$Q_g(10\text{V})$	Total Gate Charge (10V)	$V_{GS}=-10\text{V}$ , $V_{DS}=-15\text{V}$ , $I_D=-6.5\text{A}$		12.7	16	nC
$Q_g(4.5\text{V})$	Total Gate Charge (4.5V)			6.4		nC
$Q_{gs}$	Gate Source Charge			2		nC
$Q_{gd}$	Gate Drain Charge			4		nC
$t_{D(on)}$	Turn-On DelayTime	$V_{GS}=-10\text{V}$ , $V_{DS}=-15\text{V}$ , $R_L=2.5\Omega$ , $R_{GEN}=3\Omega$		7.7		ns
$t_r$	Turn-On Rise Time			6.8		ns
$t_{D(off)}$	Turn-Off DelayTime			20		ns
$t_f$	Turn-Off Fall Time			10		ns
$t_{rr}$	Body Diode Reverse Recovery Time	$I_F=-6.5\text{A}$ , $dI/dt=100\text{A}/\mu\text{s}$		22	30	ns
$Q_{rr}$	Body Diode Reverse Recovery Charge	$I_F=-6.5\text{A}$ , $dI/dt=100\text{A}/\mu\text{s}$		15		nC

A: The value of  $R_{\theta JA}$  is measured with the device mounted on 1 in<sup>2</sup> FR-4 board with 2oz. Copper, in a still air environment with  $T_A=25^{\circ}\text{C}$ . The value in any a given application depends on the user's specific board design. The current rating is based on the  $t \leq 10\text{s}$  thermal resistance rating.

B: Repetitive rating, pulse width limited by junction temperature.

C: The  $R_{\theta JA}$  is the sum of the thermal impedance from junction to lead  $R_{\theta JL}$  and lead to ambient.

D: The static characteristics in Figures 1 to 6 are obtained using  $< 300\mu\text{s}$  pulses, duty cycle 0.5% max.

E: These tests are performed with the device mounted on 1 in<sup>2</sup> FR-4 board with 2oz. Copper, in a still air environment with  $T_A=25^{\circ}\text{C}$ . The SOA curve provides a single pulse rating.

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## TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

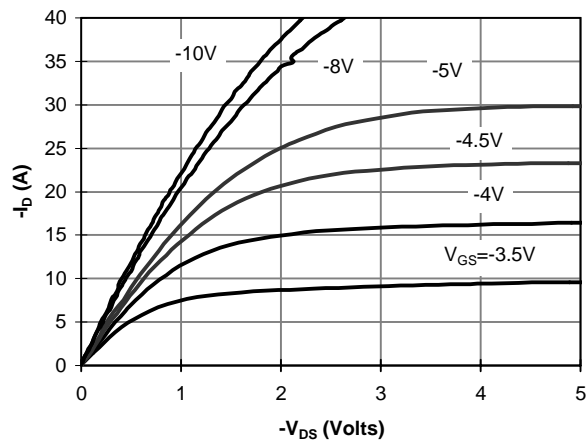


Figure 1: On-Region Characteristics

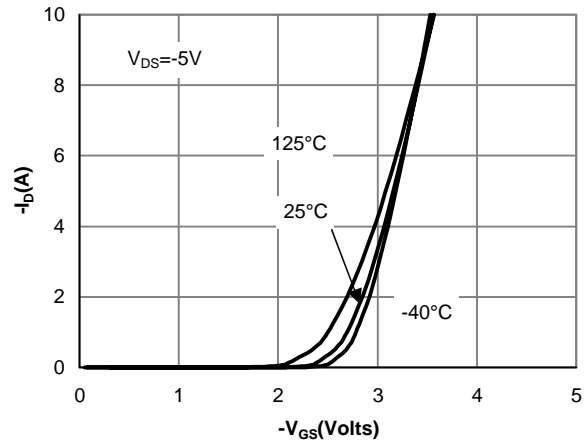


Figure 2: Transfer Characteristics

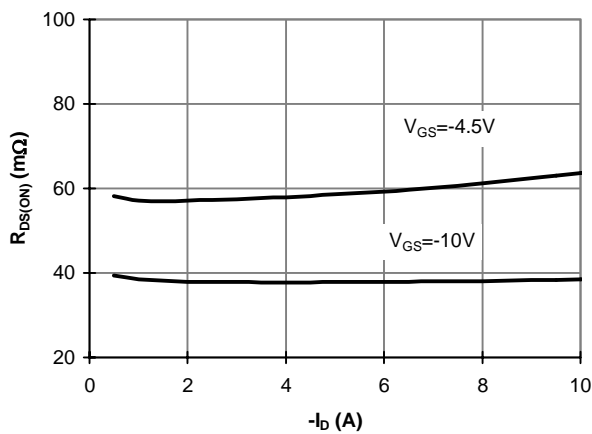


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

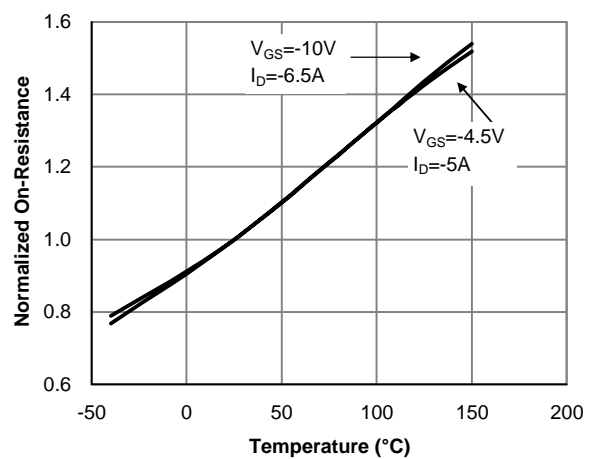


Figure 4: On-Resistance vs. Junction Temperature

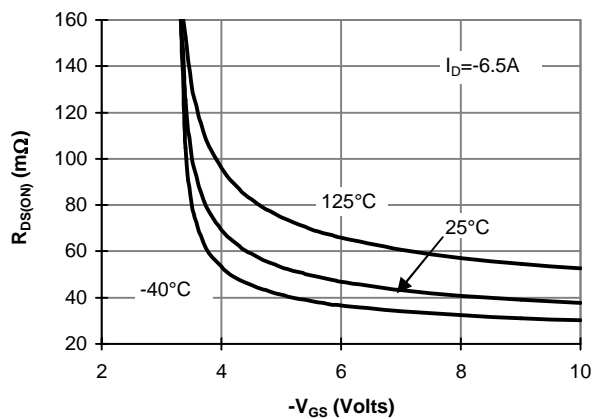


Figure 5: On-Resistance vs. Gate-Source Voltage

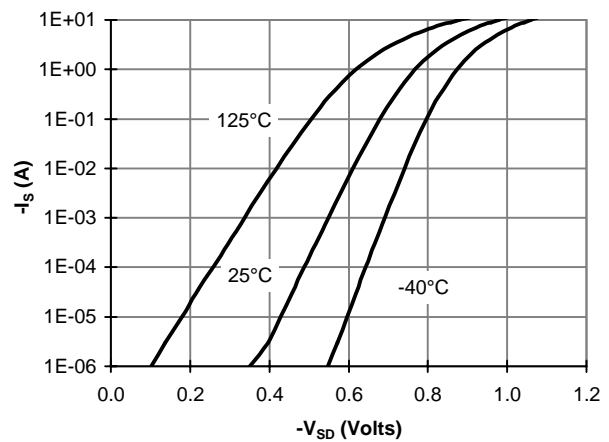


Figure 6: Body-Diode Characteristics

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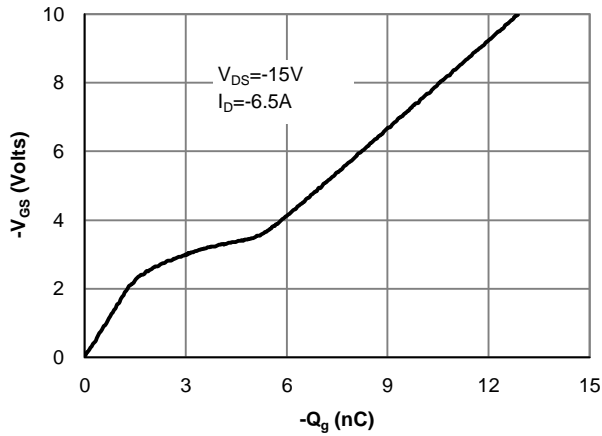


Figure 7: Gate-Charge Characteristics

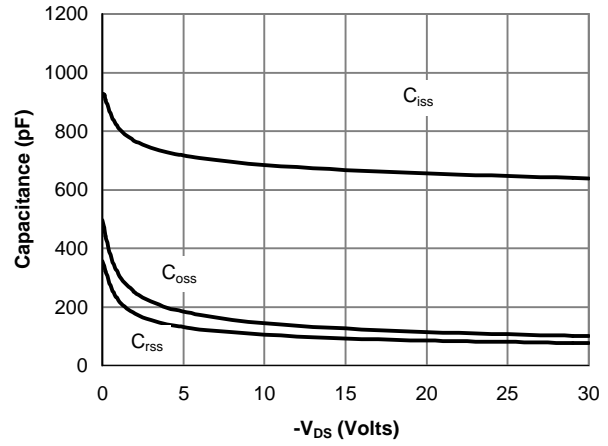


Figure 8: Capacitance Characteristics

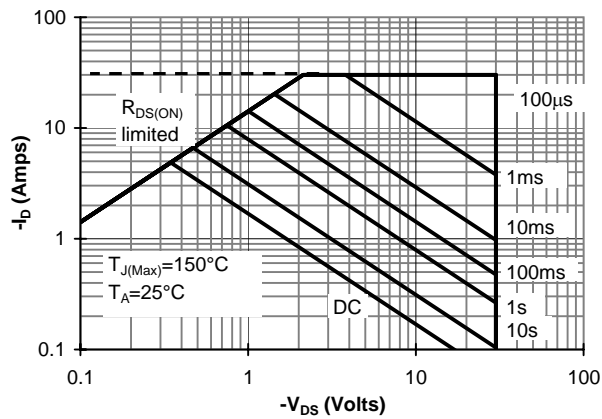


Figure 9: Maximum Forward Biased Safe Operating Area (Note E)

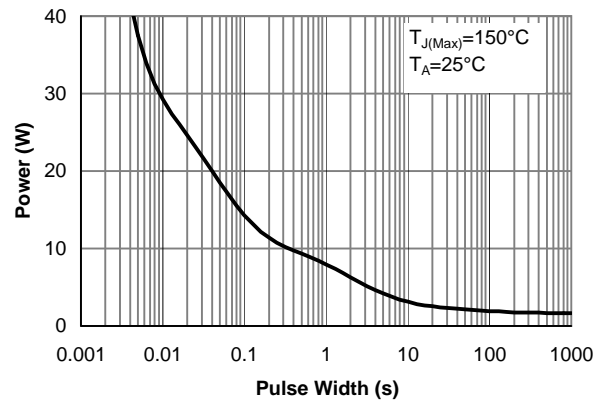


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note E)

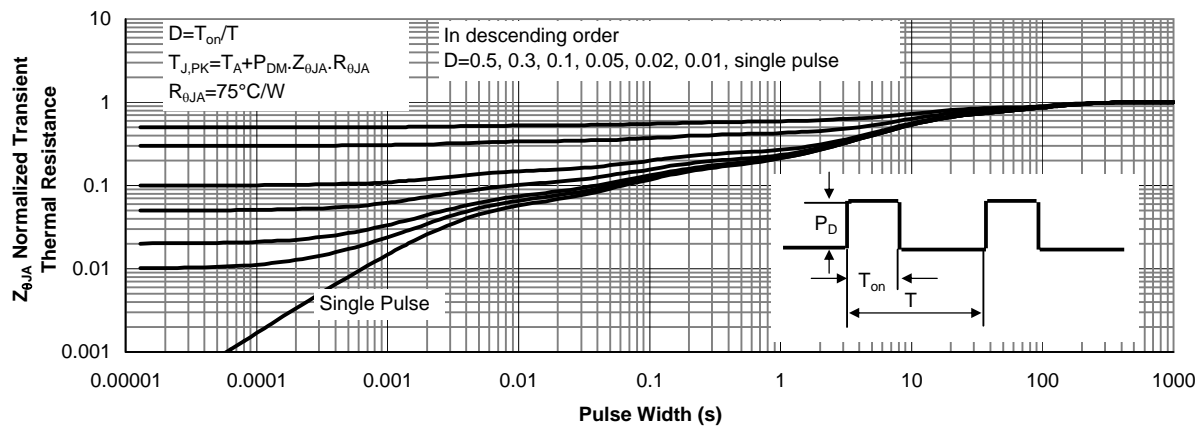


Figure 11: Normalized Maximum Transient Thermal Impedance (Note E)